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U.S. PATENT DOCUMENTS										
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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)	
/JL/	B1	WO 03/105189	12/18/2003	WO						
/JL/	B2	WO 04/001857	12/31/2003	WO						
OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)										
/JL/	C1	Boyanov, et al., "Growth of epitaxial CoSi ₂ on SiGe (001)", <u>Journal of Applied Physics</u> , American Institute of Physics. New York, US. 86(3):1355-1362 (1999).								
/JL/	C2	Buchal et al., "Ultrafast Si-based MSM mesa photodetectors with optical waveguide connection," <u>Materials Science in Semiconductor Processing</u> , 3:399-403 (2000). XP001205581								
/JL/	C3	Steegen et al., "Silicide-induced stress in Si: origin and consequences for MOS technologies," <u>Materials Science and Engineering R: Reports</u> , Elsevier Sequoia S.A., Lausanne, CH. 38(1):1-53 (2002).								
/JL/	C4	Yodo et al., "Influences of off-angle and off-direction of substrate on crystalline quality of GaAs and Ge heteroepitaxial films grown on vicinal Si (110) substrates by molecular-beam epitaxy", <u>Journal of Crystal Growth</u> . North-Holland Publishing Co., Amsterdam, NL. 209(4):724-733 (2000). XP004198396								
/JL/	C5	International Search Report for PCT/US2004/024747 dated March 22, 2005.								
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